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<input type="checkbox"/>	L5	L4 not L3	266
<input type="checkbox"/>	L4	L2 and (implant\$4 with mask\$3)	272
<input type="checkbox"/>	L3	L2 and titanium and (tantalum adj nitride)	91
<input type="checkbox"/>	L2	L1 and (overlap\$4 with gate)	707
<input type="checkbox"/>	L1	438/149,151,163,164,166,197,299,301.ccls.	3985

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		<i>DB=PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR</i>	
<input type="checkbox"/>	L2	TFT and (gate with first with conduct\$4) and (gate with second with conduct\$4) and (etch\$3 with select\$5) and (overlap\$5 with gate)	1017
<input type="checkbox"/>	L1	TFT and (titanium) and (tantalum adj nitride) and (SF6 or (sulfur adj hexafluoride))	7

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<input type="checkbox"/>	L7	L6 and (etch\$4 with (taper\$4 or angl\$4 or inclin\$6))	511
<input type="checkbox"/>	L6	L4 or L5	984
<input type="checkbox"/>	L5	L3 and inclin\$7	86
<input type="checkbox"/>	L4	L3 and (taper\$4 or angl\$4)	968
<input type="checkbox"/>	L3	L2 and LDD	1425
<input type="checkbox"/>	L2	L1 and (titanium or Ti)	2394
<input type="checkbox"/>	L1	(gate with overlap\$5) and ((hot adj carrier\$1) or (drain with field))	6518

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Freeform Search

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Display:	<input type="text" value="10"/> Documents in Display Format: <input type="text" value="TI"/> Starting with Number <input type="text" value="1"/>
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side by side		
<i>DB=USPT; PLUR=YES; OP=OR</i>		
<u>L14</u> 6872604.pn. and titanium	1	<u>L14</u>
<i>DB=PGPB,USPT; PLUR=YES; OP=OR</i>		
<u>L13</u> 6706544.pn. and titanium	1	<u>L13</u>
<u>L12</u> 6596571.pn.	1	<u>L12</u>
<u>L11</u> 6933184.pn.	1	<u>L11</u>
<u>L10</u> L9 and (ion\$1 or implant\$5)	3	<u>L10</u>
<u>L9</u> L8 and etch\$5	3	<u>L9</u>
<u>L8</u> L1 and (titanium and (tantalum adj nitride))	3	<u>L8</u>
<u>L7</u> L5 and SF6	1	<u>L7</u>
<u>L6</u> L5 and (sulfur adj hexafluoride)	0	<u>L6</u>
<u>L5</u> L4 and (selectiv\$5 with etch\$6)	7	<u>L5</u>
<u>L4</u> L3 and (titanium and (tantalum adj nitride))	7	<u>L4</u>
<u>L3</u> L1 or L2	11	<u>L3</u>
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(20040140472 or 20030100151 or 20030062524 or 20030020118 or		

L2 20020163049 or 20020000576 or 20010055841 or 20010048408).pn.

8 L2

DB=USPT; PLUR=YES; OP=OR

L1 (6706544 or 6933184 or 6872604).pn.

3 L1

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<input type="checkbox"/>	L2	L1 and (overlap\$4 or taper\$4).clm.	35
<input type="checkbox"/>	L1	438/163.ccls.	288

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IEEE JNL IEEE Journal or Magazine

IEE JNL IEE Journal or Magazine

IEEE CNF IEEE Conference Proceeding

IEE CNF IEE Conference Proceeding

IEEE STD IEEE Standard

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1. Analysis of electrical characteristics of gate overlapped lightly doped drain (GOLDD) polysil transistors with different LDD doping concentration

Bonfiglietti, A.; Cuscuna, M.; Valletta, A.; Mariucci, L.; Pecora, A.; Fortunato, G.; Brotherton, S.D.; /

Electron Devices, IEEE Transactions on

Volume 50, Issue 12, Dec. 2003 Page(s):2425 - 2433

Digital Object Identifier 10.1109/TED.2003.819250

[AbstractPlus](#) | [References](#) | Full Text: [PDF](#)(672 KB) IEEE JNL

2. Improved lifetime of poly-Si TFTs with a self-aligned gate-overlapped LDD structure

Mishima, Y.; Ebiko, Y.;

Electron Devices, IEEE Transactions on

Volume 49, Issue 6, June 2002 Page(s):981 - 985

Digital Object Identifier 10.1109/TED.2002.1003716

[AbstractPlus](#) | [References](#) | Full Text: [PDF](#)(234 KB) IEEE JNL

3. Hot carrier-induced degradation of gate overlapped lightly doped drain (GOLDD) polysilicon

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4. A new dopant activation technique for poly-Si TFTs with a self-aligned gate-overlapped LDD

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5. A high speed and high reliability MOSFET utilizing an auxiliary gate

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VLSI Technology, 1990. Digest of Technical Papers. 1990 Symposium on

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IEEE JNL	IEEE Journal or Magazine
IEE JNL	IEE Journal or Magazine
IEEE CNF	IEEE Conference Proceeding
IEE CNF	IEE Conference Proceeding
IEEE STD	IEEE Standard

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1. Gated-four-probe a-Si:H thin-film transistor structure

Chun-Ying Chen; Chun-Sung Chiang; Kanicki, J.;

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Bonfiglietti, A.; Cuscuna, M.; Valletta, A.; Mariucci, L.; Pecora, A.; Fortunato, G.; Brotherton, S.D.;
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